

Citations for Target : Ge

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1951	Heller, Z. H. Tendam, D. J. 'The Stopping Power of Metals and Semiconductors' <i>Phys. Rev., 84, 905-09 (1951)</i> <i>Comment : S. 9 MeV D -> Si, Ni, Cu, Ge, Zr, Rh, Ag, Sn, Air Rel. To Al</i>	1951-Hell 0067
1955	Green, D. W. Cooper, J. N. Harris, J. C. 'Stopping Cross Section of Metals for Protons of Energies from 400 to 1000 keV' <i>Phys. Rev., 98, 466-70 (1955)</i> <i>Comment : S. 0.4-1.0 MeV H -> Mn, Cu, Ge, Sn, Se, Ag, Sb, Au, Pb, Bi</i>	1955-Gree 0059
1956	Gobeli, G. W. 'Range-Energy Relation for Low-Energy Alpha Particles in Si, Ge and Insb' <i>Phys. Rev., 103, 275-78 (1956)</i> <i>Comment : R. 0.70-4.45 MeV He -> Si, Ge, InSb, Al, Cu, Ag, Au.</i>	1956-Gobe 0056
1957	Bredov, M. M. Okuneva, N. M. 'On the Penetration of Ions of Medium Energy in Matter (In Russian)' <i>Dokl. Akad. Nauk. Sssr, 113, 795-96 (1957)</i> <i>Comment : R. 4 keV Cs -> Ge</i>	1957-Bred 0197
1958	Bredov, M. M. Lang, J. G. Okuneva, N. M. 'On the Problem of Penetration of Medium-Energy Ions into Matter' <i>Zh. Tek. Fiz., 28, 252-53 (1958) [Engl. Trans. Sov. Phys. Tech. Phys., 3, 228-29, (1958)]</i> <i>Comment : R. 4 keV Cs -> Ge</i>	1958-Bred 0198
1962	Davies, J. A. McIntyre, J. D. Sims, G. 'The Range of Cs137 Ions of Low keV Energies in Germanium' <i>Can. J. Chem., 40, 1605-10 (1962)</i> <i>Comment : R. 4-20 keV 137Cs -> Ge.</i>	1962-Davi 0559
1962	Gott, Yu. V. Telkovskiy, V. G. 'Energy Losses of Light Ions in Thin Metallic Foils' <i>Radioteknika I. Elek. (USSR), 7, 1956-61 (1962) [Engl. Trans:Rad. Eng. and Electron Phys., 7, 1813-19 (1962)]</i> <i>Comment : S. 2-15 keV H, D, He -> Al, Ti, Cu, Ge, Ag, Sn, Au</i>	1962-Gott 0159
1964	Pavlov, P. V. Zorin, E. I. Tetelbaum, D. I. Popov, Ya. S. 'The Depth of Penetration and the Distribution of Radiation Defects in Germanium Bombarded by Argon and Nitrogen Ions' <i>Fiz. Tverd. Tela, 6, 3222-26 (1964). [Engl. Trans. Sov. Phys. Solid State, 6, 2577-80 (1964)].</i> <i>Comment : R. 46-82 keV Ar, N -> Ge</i>	1964-Pavl 0769

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1964	Wikner, E. G. Horiye, H. Nichols, D. K. 'Elastic Versus Inelastic Energy Loss of Recoil Germanium and Silicon Atoms' <i>Phys. Rev. A, 136, 1428-32 (1964)</i> Comment : S, Eta(Epsilon). 68-157 keV Si -> Si, 19-36 keV Ge -> Ge	1964-Wikn 0829
1965	Chasman, C. Jones, K. W. Ristinen, R. H. 'Measurement of the Energy Loss of Germanium Atoms to Electrons in Germanium at Energies Below 100 keV' <i>Phys. Rev. Letters, 15, 245-48 (1965) (Erratum, Phys. Rev. Letters, 15, 684,(1965)</i> Comment : S, Eta(Epsilon). 20-100 keV Ge -> Ge	1965-Chas 0226
1965	Sattler, A. R. Dearnaley, G. 'Anomalous Energy Losses of Protons Channeled in Single Crystal Germanium' <i>Phys. Rev. Letters, 15, 59-61 (1965)</i> Comment : S, dS. 4.25 - 7.75 MeV H, 7.63 MeV D -> Ge (Cryst.)	1965-Satt2 0252
1966	Appleton, B. R. Altman, M. Feldman, L. C. Gibson, W. M. Erginsoy, C. 'Least Energy Loss and Its Dispersion for pChanneled Protons in Silicon and Germanium Single Crystals' <i>Bull. Am. Phys. Soc., 11, 176 (1966)</i> Comment : S, dS. 3-11 MeV H -> Si, Ge (Both Cryst.)	1966-Appl 0257
1966	Sattler, A. R. Vook, F. L. Palms, J. H. 'Ionization Produced by Energetic Germanium Atoms Within a Germanium Lattice' <i>Phys. Rev., 143, 588-95 (1966)</i> Comment : S, Eta(Epsilon). 21-997 keV Ge -> Ge	1966-Satt 0246
1967	Appleton, B. R. Erginsoy, C. Gibson, W. M. 'Channeling in the Energy Loss of 3-11 MeV Protons in Silicon and Germanium Single Crystals' <i>Phys. Rev., 161, 330-49 (1967)</i> Comment : S. 3-11 MeV H -> Si, Ge (Both Cryst.). Chann. And Random	1967-Appl 0305
1967	Chasman, C. Jones, K. W. Ristinen, R. A. Sample, J. T. 'Measurement of Energy Loss of Germanium Atoms to Electrons in Germanium at Energies Below 100 keV' <i>Phys. Rev., 154, 239-44 (1967)</i> Comment : S, Eta(Epsilon). 20-100 keV Ge -> Ge	1967-Chas 0283
1967	Marcinkowski, A. Rzewuski, H. Werner, Z. 'Range-Energy Relation for Low Energy Protons in Si and Ge' <i>Nucl. Inst. Methods, 57, 338-40 (1967)</i> Comment : R. 0.8 - 1.9 MeV H -> Ge, Si.	1967-Marc 0312

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1968	Chasman, C. Jones, K. W. Kramer, H. W. Brandt, W. 'Band-Gap Effects in the Stopping of Ge72* Atoms in Germanium' <i>Phys. Rev. Letters</i> 22, 1430-33 (1968) <i>Comment : S. Eta(Epsilon). 10-30 keV Ge -> Ge</i>	1968-Chas 0840
1968	Sattler, A. R. Dearnaley, G. 'Channeling in Diamond-Type and Zinc-Blende Lattices: Comparative Effects in Channeling of Protons and Deuterons in Ge, GaAs, and Si' <i>Phys. Rev., 161, 244-52 (1967)(Erratum, Phys. Rev., 165, 750 (1968))</i> <i>Comment : S. 4-7.6 MeV H, D -> Ge, GaAs, Si (All Cryst.)</i>	1968-Satt 0308
1968	Shipatov, E. T. Kononov, B. A. 'Investigation of the Channeling of Protons in Single Crystals of Ionic Compounds and Semiconductors' <i>Izv. Vuz. Fiz. No. 9, 52-56 (1968). [Engl. Trans. Soviet Phys. J. No. 9, 46-49, (1968)]</i> <i>Comment : S, dS. H (4.7-6.7 MeV) -> NaCl, KCl, KBr, Si, Ge (crystals)</i>	1968-Ship2 0599
1968	Shipatov, E. T. Kononov, B. A. 'Energy Distribution of 6.72 MeV Protons Passing through Monocrystals.' <i>Atomnaya Energiya (USSR), 25, 439-40 (1968) [Engl. Trans. Sov. Atom. Energy, 25, 1254-55 (1968).]</i> <i>Comment : S, dS. 6.72 MeV H -> NaCl, KCl, KBr, Si, Ge (All Cryst.)</i>	1968-Ship3 0653
1969	Arkhipov, E. P. Gott, Yu. V. 'Slowing Down of 0.5 - 30 keV Protons in Some Materials.' <i>Zh. Eksp. Teor. Fiz., 56, 1146-51 (1969). [Engl. Trans. Sov. Phys. Jetp, 29, 615-18 (1969)]</i> <i>Comment : S. 0.5-30 keV H -> C, Ti, Al, Cu, Ni, Fe, Ge, Si, Sb, Bi</i>	1969-Arkh 0410
1969	Chu, W. K. Powers, D. 'Alpha-Particle Stopping Cross Sections in Solids from 400 keV to 2 MeV' <i>Phys. Rev., 187, 478-90 (1969)</i> <i>Comment : S. 0.4-2.0 MeV He -> Be, C, Mg, Al, Ti, V, Cr, Mn, Fe, Co, Ni, Cu, Ge, Pd, Ag, In, Sn</i>	1969-Chu 0382
1969	Gorodetzky, S. Pape, A. Coopermann, E. L. Chevallier, A. Sens, J. C. 'Pouvoir D'Arret Du Germanium Pour Des Protons D'Energie Comprise Entre 0.5 et 5.5 MeV' <i>Nucl. Inst. Methods, 70, 11-12 (1969)</i> <i>Comment : S. 0.36 - 5.5 MeV H -> Ge</i>	1969-Goro 0387
1969	Shipatov, E. T. 'Energy and Angular Distributions of Protons Transmitted by Germanium and Silicon Single Crystals Along (110) and (100) Channels in the Crystal Lattice' <i>Fiz. Tekh. Poluprovodnikov, 2, 1690-91 (1968). [Engl. Trans. Sov. Phys. Semicond., 2, 1408-09 (1969)]</i> <i>Comment : S, dS. 6.72 MeV H -> Si, Ge (Both Cryst.)</i>	1969-Ship2 0654

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1970	Apel, D. Muller-Jahreis, U. Schwabe, S. 'On the Z2-Dependence of Electronic Stopping Cross Section' <i>Phys. Stat. Sol. A, 3, K173-75 (1970)</i> <i>W. Palmer, M. W. Thompson, P. D. Townsend: Atomic Collision Phenomena in Solids. North-Holland, Amsterdam, P. 388-99 (1970)</i> <i>Comment : S. 10-100 keV Li -> Si, V, Cr, Fe, Ge, Se</i>	1970-Apel 0655
1970	Clark, G. J. Morgan, D. V. Poate, J. M. 'Energy Loss of Channeled Protons in the MeV Region, in D' <i>W. Palmer, M. W. Thompson, P. D. Townsend: Atomic Collision Phenomena in Solids. North-Holland, Amsterdam, P. 388-99 (1970)</i> <i>Comment : S, dS. (4-8 MeV) H -> SiC, W, Fe, Ge, Mo, NaCl, MgO (All Targets Cryst.)</i>	1970-Clar 0391
1971	Jones, K. W. Kraner, H. W. 'Stopping of 1- to 1.8 keV 73Ge Atoms in Germanium.' <i>Phys. Rev. C, 4, 125-29 (1971)</i> <i>Comment : S. Eta(Epsilon) 1-1.8 keV 73Ge -> Ge</i>	1971-Jone 0672
1972	Carter, G. Baruah, J. N. Grant, W. A. 'The Collection of Ions Implanted in Semiconductors: II: Range Distributions Derived from Collection and Sputter-Etch Curves.' <i>Rad. Effects, 16, 107-114 (1972)</i> <i>Comment : R. 10-30 keV Kr, Tl -> GaAs, GaP, Ge, Si</i>	1972-Cart 0976
1972	Minear, R. L. Nelson, D. G. Gibbons, J. F. 'Enhanced Diffusion in Si and Ge by Light Ion Implantation' <i>J. Appl. Phys., 43, 3468-3480 (1972)</i> <i>Comment : R, dR. 70-150 keV H, D, H2 -> Si, Ge</i>	1972-Mine 0999
1972	Ward, D. Graham, R. L. Geiger, J. S. 'Measurement of Stopping Power for 4He, 16O and 35Cl Ions at =1 to =3 MeV Per Nucleon in Ni, Ge, Y, Ag, and Au' <i>Can. J. Phys., 50, 2302-12 (1972)</i> <i>Comment : S. 3-15 MeV He, 8-66 MeV O, 10-90 MeV 35Cl -> Ni, Ge, Y, Ag, Au</i>	1972-Ward 0434
1972	Whitton, J. L. Carter, G. Baruah, J. N. Grant, W. A. 'The Collection of Ions Implanted in Semiconductors: I Saturation Effects.' <i>Rad. Effects, 16, 101-105 (1972)</i> <i>Comment : R, dR. 10-30 keV Kr, Tl -> Si, Ge, GaP, GaAs</i>	1972-Whit 0975
1973	Chu, W. K. Ziegler, J. F. Mitchell, I. V. Mackintosh, W. D. 'Energy-Loss Measurements of 4He Ions in Heavy Metals' <i>Appl. Phys. Letters, 22, 437-39 (1973)</i> <i>Comment : S. 2.0 MeV He -> Al, Si, V, Fe, Co, Ni, Cu, In, Ge, Mo, Sb, Te, Gd, Hf, Ta, W, Ir, Pt, Au, Pb</i>	1973-Chu 3 0124
1973	Lin, W. K. Olson, H. G. Powers, D. 'Alpha-Particle Stopping Cross Sections of Silicon and Germanium' <i>J. Appl. Phys., 44, 3631-34 (1973)</i> <i>Comment : S. 0.3-2.0 MeV He -> Si, Ge (Amorph.)</i>	1973-Lin 0497

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1974	Macdonald, P. J. Palmer, D. W. 'Differences in Defect Production and Annealing Processes in Boron- and Carbon-Irradiated Germanium' <i>Stuttgart, Et. Al., Lattice Defects in Semiconductors, Intl. Conf. on Semiconductors, 504-12 (1974)</i> Comment : R, dR. 60 keV 11B, 12C -> Ge	1974-Macd 1269
1975	Holmen, G. Buren, A. Hogberg, P. 'Radiation Damage in Ge Produced and Removed by Energetic Ge Ions' <i>Rad. Effects, 24, 51-8 (1975)</i> Comment : R, dR. Ge (40 KeV) -> Ge	1975-Holm 1274
1975	Jones, K. W. Kraner, H. W. 'Energy Lost to Ionization by 254-eV 73Ge Atoms Stopping in Ge' <i>Phys. Rev. A, 11, 1347-53 (1975)</i> Comment : S. Eta(Epsilon) 254 eV 73Ge -> Ge	1975-Jone 0664
1975	Neshev, F. G. Puzanov, A. A. Shyshkin, K. S. Sirotinin, E. I. Tulinov, A. F. 'The Determination of Energy Losses of Nitrogen Ions from Backscattering Spectra' <i>Rad. Effects, 25, 271-73 (1975)</i> Comment : S. 1.0-7.4 MeV N -> Ti, Ge, Ni, Ag, Au, W	1975-Nesh 0782
1975	Oetzmann, H. Feuerstein, A. Grahmann, H. Kalbitzer, S. 'Range Parameters of Heavy Ions in Amorphous Targets at LSS-Energies of 0.0006 < Epsilon < 0.3.' <i>Phys. Letters, 55A, 170-172 (1975)</i> Comment : R, dR. 1-60 keV As, Ge, Sb, Au, Bi -> Si, Ge, Al	1975-Oetz 1182
1975	Schuch, R. 'Blocking-Effekte Bei Transmission von Alpha-Teilchen Durch Germanium - und Siliziumkristalle' <i>Z. Physik A, 272, 61-66 (1975)</i> Comment : S. 8.8 MeV He -> Si, Ge (Cryst.)	1975-Schu 0516
1975	Simons, D. G. Land, D. J. Brennan, J. G. Brown, M. D. 'Range, Distribution and Stopping Power of 800-keV 14N+ Ions Implanted in Metals from Z2 = 22 to Z2 = 32' <i>Phys. Rev. A, 12, 2383-92 (1975)</i> Comment : R, dR, S. 800 keV N -> Ti, V, Cr, Mn, Fe, Co, Ni, Cu, Zn, Ga, Ge	1975-Simo 0798
1976	Benmalek, M. Thomas, J. P. Mackowski, J. M. 'Ion-Bombardment of Amorphous Semiconductors and Related Evolution of Structural and Electrical Properties' <i>Ion Implantation in Semiconductors, Ed. by F. Chernow, J. A. Borders, D. K. Brice, 637-647 (1976)</i> Comment : R. 20-300 keV Ne, Ar, Ge, Cd, Te, Xe, Au -> Ge	1976-Benm 1068

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1976	Fich, O. Golovchenko, J. A. Nielsen, K. O. Uggerhoj, E. Vraast-Thomsen, C. 'Ionization Loss of Channeled 1.36 GeV/c Protons and Pions.' <i>Phys. Rev. Letters, 36, 1245-48 (1976)</i> Comment : S. 1.35 GeV/c H, Pi -> Ge (Cryst. Chan. And Random)	1976-Fich 0874
1976	Kovaleva, E. A. Korol, V. M. Merrik, B. R. 'Ranges of Metals in Amorphous Si and Ge' <i>Elektronnaya Texnika, 2, 33-38 (1976)</i> Comment : R, dR. 10-200 keV Li, Na, K, Rb, Cs -> Si, Ge, Al, Ni	1976-Kova 0944
1976	Land, D. J. Simons, D. G. Brennan, J. G. Brown, M. D. 'Unfolding Techniques for the Determination of Distribution Profiles from Resonance Reaction Gramma-Ray Yields' <i>O. Meyer, G. Linker, F. Kappeler (Ed.): Ion Beam Surface Layer Analysis. Plenum, N.Y., 851-61 (1976)</i> Comment : R, dR. 800 keV N -> Z2 = 22-32, 40-42	1976-Land 0808
1976	Neuwirth, W. Pietsch, W. Hauser, U. 'Stopping Cross Sections of Elements with Z=2 to 87 for Li Ions with Energies Between 80 keV and 840 keV' <i>Physics Data, Erstes Phsikalischs Institut, Univ. Zu Koln, Germany (1976)</i> Comment : S. 80-840 keV Li -> (2 <= Z2 <= 87)	1976-Neuw 1178
1976	Oetzmann, H. Feuerstein, A. Grahmann, H. Kalbitzer, S. 'Range Parameters of Heavy Ions in Silicon and Germanium with Released Energies from 0.01 < epsilon < 10' <i>Meyer, G. Linker and F. Kappeler (Ed.): Ion Beam Surface Layer Analysis, Plenum, N.Y., P. 245-54 (1976)</i> Comment : R, dR. (1-40 keV) Al, Sb, As, Ge, Au, Bi -> Si, Ge	1976-Oetz 0845
1976	Simons, D. G. Land, D. J. Brennan, J. G. Brown, M. D. 'Z2 Dependence of the Electronic Stopping Power of 800 keV 14N+ Ions in Targets from Carbon through Molybdenum' <i>Meyer, G. Linker and F. Kappeler (Ed.): Ion Beam Surface Layer Analysis, Plenum, N.Y., P. 863-71 (1976)</i> Comment : S. 800 keV N -> Z2 = 22-32, 40-42	1976-Simo2 0848
1977	Bogh, E. Hogild, P. Stensgaard, I. 'Spatial Distribution of Defects in Ion Bombarded Silicon and Germanium' <i>Rad. Effects, 7, 115-121 (1977)</i> Comment : R. 10-400 keV P, Sb -> Si, Ge	1977-Bogh 0968
1977	Hale, J. A. Stephens, G. A. 'The Scattering of 2 MeV He+ in Amorphous Germanium' <i>Rad. Effects, 33, 29-34 (1977)</i> Comment : R, dR. 200-400 keV N -> Ge	1977-Hale 1258

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1978	Eckardt, J. C. 'Energy Loss and Straggling of Protons and Helium Ions Traversing Some Thin Solid Foils' <i>Phys. Rev. A, 18, 426-433 (1978)</i> Comment : S, dS. 20-260 keV H, He -> Ge, Se, Pd, Ag, Sb, Bi	1978-Ecka2 1154
1978	Marshall, R. E. ElFiqi, A. R. Kliwer, J. K. 'Measurement of Stopping Powers using Ion-Induced X-Ray Emission' <i>Nucl. Inst. Methods, 150, 241-245 (1978)</i> Comment : S. 100 keV H -> Sc, Ni, Cu, Ge	1978-Mars 1085
1978	Oetzmann, H. Kalbitzer, S. '⁴He Stopping Power Measurements by using Ion Implantation and Backscattering Techniques' <i>Intl. Conf. Ion Beam Modification of Materials, Budapest -d (1978)</i> Comment : S. 0.15-1 MeV He -> C, Ge, Si	1978-Oetz 1134
1978	Rud, N. Bottiger, J. Jensen, P. S. 'Measurements of Energy-Loss Distributions for 6.5 MeV ¹⁵N in Solids.' <i>Nucl. Inst. Methods, 151, 247-252 (1978)</i> Comment : S, dS. 6.5 MeV ¹⁵ N -> C, Al, Cu, Ge, Ag, Sn, Bi	1978-Rud 1104
1978	Vedmanov, G. D. Neshov, F. G. Puzanov, A. A. Urmanov, A. R. 'Determining Stopping Power from Spectra of Backscattered Ions' <i>Sov. Atom. Energy, 45, 989-991 (1978)</i> Comment : S. N (0.75-7.4MeV) -> Fe, Ge, GaAs, FeGe2	1978-Vedm 1537
1979	Chumanov, V. Ya. Izmailov, Sh. Z. Pokhil, G. P. Sirotinin, E. I. Tulinov, A. F. 'On the Determination of Energy Losses by Charged Particles from the Backscattered Energy Spectra' <i>Phys. Stat. Sol. A, 53, 51-62 (1979)</i> Comment : S. 0.1-1.4 MeV H -> W, 0.1-0.25 MeV H -> Ge	1979-Chum 1236
1979	Ved'manov, G. D. Gavrilov, F. F. Mizgulin, V. N. Neshov, F. G. Puzanov, A. A. 'Energy Loss of Carbon Ions in Titanium, Nickel and Germanium' <i>Sov. Phys. J., 22, 668-669 (1979)</i> Comment : S. C (0.6-7 MeV) -> Ti, Ni, C.	1979-Ved 1955
1979	Ved'manov, G. D. Gavrilov, F. F. Mizgulin, V. N. Neshov, F. G. Puzanov, A. A. 'Energy Loss of Carbon Ions in Titanium, Nickel and Germanium' <i>Izv. Vys. Uch. Zav. Fiz., 22, 111 (1979). English transl.: Sov. Phys. J., 22, 668 (1979)</i> Comment : S. C (0.8-9 MeV) -> Ti, Ni, Ge	1979-Ved 2 1783
1980	Hamm, R. N. Turner, J. E. Wright, H. A. Ritchie, R. H. 'Heavy-Ion Track Structure in Silicon' <i>Preprint (1980) 2</i> Comment : R, dR. 800 keV N -> Z2 = 22-32, 40-42	1980-Hamm 1352

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1980	Izmailov, Sh. Z. Sirotinin, E. I. Tulinov, A. F. 'Energy Loss of Protons in Si, Ge, and Mo' <i>Nucl. Inst. Methods, 168, 81-84 (1980)</i> <i>Comment : S, dS. .1-1 MeV H -> Si, Ge, Mo</i>	1980-Izma 1342
1980	Kalitzer, S. Oetzmamn, H. 'Ranges and Range Theories' <i>Rad. Effects, 47, 57-72, (1980)</i> <i>Comment : R, dR. .1-2 MeV Bi, Sb, As, Ge, P, Au, Cs, Eu, Gd Tb -> Si, Ge, C, Al</i>	1980-Kalb 1323
1980	Land, D. J. Simons, D. G. Brennan, J. G. Brown, M. D. 'Z2 and Energy Dependence of Range Distributions and Stopping Powers for Nitrogen Ions in Solids' <i>Phys. Rev. A, 22, 68-75 (1980)</i> <i>Comment : S,R,dR. 25-2000 keV N -> Fe, Ni, Zr, Au, Ti, V, Cr, Mn, Co, Ni, Cu, Zn, Ga, Ge, Nb, Mo, Tc, Ru, Rh, Pd, Ag, Cd, In, Sn, Sb, Te</i>	1980-Land2 1373
1980	Land, D. J. Simons, D. G. Brennan, J. G. Brown, M. D. 'Z2 and Energy Dependence of Range Distributions and Stopping Powers for Nitrogen Ions in Solids' <i>Phys. Rev. A, 22, 1, 68-75 (1980)</i> <i>Comment : S,R, dR. N (800 keV) -> 24 Solids (C-Pb)</i>	1980-Land3 1453
1980	Littmark, U. Hofer, W. O. 'Recoil Mixing in High-Fluence Ion Implantation' <i>Nucl. Inst. Methods, 170, 177-181 (1980)</i> <i>Comment : R, dR. 5-50 keV Kr -> Ge</i>	1980-Litt 1375
1980	Oetzmamn, H. Kalitzer, S. 'He4-Stopping Power Measurements by using Ion Implantation and Backscattering Techniques' <i>Rad. Effects, 47, 73-80 (1980)</i> <i>Comment : S, dS. 0-1E5 keV He -> C, Si, Ge</i>	1980-Oetz 1324
1983	Fink, D. Biersack. J. P. Stadele, M. Tjan, K. Cheng, V. K. 'Nitrogen Depth Profiling using the N(n,p)C Reaction' <i>Nucl. Inst. Methods, 218, 171-175 (1983)</i> <i>Comment : R. N(1.5 MeV) -> Al, Si, Fe, Ni, Cu, Co, Ge, Zr, Nb, Mo, Sn, Pb</i>	1983-Fink2 2117
1983	Mannsperger, H. Kalitzer, S. Demond, F. J. Damjantschitsch, H. 'Projection Factors of Low Energy Ion Ranges' <i>Nucl. Inst. Methods, 209/210, 49-55 (1983)</i> <i>Comment : R. H, C, Na, Al, Si, Ar, Cr (.04<epsilon<1) -> Si, Ge</i>	1983-Mann 2199
1984	Sirotinin, E. I. Tulinov, A. F. Khodyrev, V. A. Mizgulin, V. N. 'Proton Energy Loss in Solids' <i>Nucl. Inst. Methods, B4, 337 (1984) -1</i> <i>Comment : S. H (0.1-6.0 MeV) -> Al, Si, Sc, V, Cu, Zn, Ga, Ge, Y, Zr, Nb, Mo, Ag, Cd, In, Sn, La, Sm, Gd, Yb, Hf, Ta, W, Pt, Au, Pb</i>	1984-Siro 1770

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1985	Land, D. J. Simons, D. G. Brennan, J. G. Glass, G. A. 'Range Distributions and Electronic Stopping Power of Nitrogen Ions in Solids' <i>Nucl. Inst. Methods, B10/11, 234-236 (1985)</i> Comment : <i>S, R, dR, N (800 keV) -> 24 Solids (C-Pb)</i>	1985-Land 1454
1986	Izsak, K. Berthold, J. Kalbitzer, S. 'Range Phenomena of Low Energy Ions in Solids' <i>Nucl. Inst. Methods, B15, 34-41 (1986)</i> Comment : <i>R, In, Xe, Pb, Cs, Au, (.01 < epsilon < 1) -> Al, Si, Ni, Ri, Ge, Al2O3</i>	1986-Izsa 2198
1987	Fink, D. Biersack, J. P. Stadele, M. Cheng, V. K. 'Range Profiles of Helium in Solids' <i>Rad. Effects, 104, 1-42 (1987)</i> Comment : <i>R, He-3 (50-1500 keV) -> Be, C, Mg, Al, Si, Ti, V, Mn, Fe, Ca, Ni, Cu, Zn, Ge, Zr, Nb, Mo, Ag, Cd, In, Sn, Sb, Tb, Dy, Er, Ta, W, Ir, Pt, Au, Pb, Bi, SiC, MnO2</i>	1987-Fink 1645
1990	Arstila, K. Keinonen, J. Tikkainen, P. 'Stopping Power for Low Velocity Heavy Ions: 0-1.0 MeV Mg Ions in 17 (z2=22-79) Elemental Solids' <i>Phys. Rev. B, 41, 6117-6123 (1990)</i> Comment : <i>S, Mg (0-1.0 MeV/amu) -> Ti, V, Fe, Co, Ni, Cu, Ge, Nb, Mo, Pd, Ag, Hf, Ta, W, Re, Pt, Au</i>	1990-Arst 1923
1991	Arstila, K. Keinonen, J. Tikkainen, P. 'Stopping Power for Low-Velocity Mg Ions in Si, Ge and GaAs' <i>Phys. Rev. B, 43, 13967-13970 (1991)</i> Comment : <i>S, Mg (0-0.8 MeV/amu) -> Si, Ge, GaAs</i>	1991-Arst 1910
1992	Eppacher, C. Semrad, D. 'The Effective Charge of He Ions in Metals' <i>Nucl. Inst. Methods, B67, 138-141 (1992)</i> Comment : <i>S, H, He (1-2.5 Vo) -> Ge, Sn and Pb</i>	1992-Eppa 1898
1992	Eppacher, Ch. Semrad, D. 'Dependence of Proton and Helium Energy Loss in Solids upon Plasma Properties' <i>Nucl. Inst. Methods, B69, 33-38 (1992)</i> Comment : <i>S, H, He (20-250 keV/amu) -> Au, Cr, Ag, Al, Ge, Sn, Pb</i>	1992-Eppa2 2161
1992	Gunzler, R. Weiser, M. Kalbitzer, S. '3-D Concentration Distributions of Ion Implants' <i>Nucl. Inst. Methods, B62, 350-355 (1992)</i> Comment : <i>R, H, N, Si (.1-6 MeV) -> Ge. 3-D profiles.</i>	1992-Gunz 2194
1992	Keinonen, J. Arstila, K. Tikkainen, P. 'Electronic Stopping Power of Si and Ge for MeV Energy Si Ions' <i>Appl. Phys. Letters, 60, 228-230 (1992)</i> Comment : <i>S, Si, P (0-30 MeV) -> Si, Ge</i>	1992-Kein 1901

Citations for Target : Ge

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
1992	Schule, V. Gunzler, R. Oberschachtsiek, P. Weiser, M. Kalbitzer, S. 'Range Parameters of Deep Ion Implants in Group IV Semiconductors' <i>Nucl. Inst. Methods, B62, 338-345 (1992)</i> <i>Comment : R. Ranges of Heavy Ions (1 MeV/amu) -> C, Si, Ge</i>	1992-Schu 2195
1995	Khawaja, E. E. Durrani, S. M. A. Hallak, A. B. Daous, M. A. 'Measurements of Absolute Stopping Cross Sections by Backscattering in Thin Dielectric Films' <i>Nucl. Inst. Methods, B95, 153-157 (1995)</i> <i>Comment : S. He (0.6-1.8 MeV) -> ZnSe, ZnS, Ge, TiO2, MoO3</i>	1995-Khaw 0896
1996	Ikeda, A. Sumitomo, K. Nishioka, T. Kido, Y. 'Stopping Powers and Energy Straggling for 50-300 keV H in Amorphous Si and Ge Films' <i>Nucl. Inst. Methods, B115, 34-38 (1996)</i> <i>Comment : S, dS. H (50-300 keV) -> Si, Ge</i>	1996-Iked 2029
2006	Weijers-Dall, T. D. Timmers, H. Stenstrom, K. Persson, P. Pergjegjaj, A. 'Measurements of the Stopping Forces for Heavy Ions in Ge, Ag and Au using Novel "Polka-Dot" Detectors' <i>Nucl. Inst. Methods, B251, 352,360 (2006)</i> <i>Comment : S, C, N, O -> Ge, Ag, Au</i>	2006-Weij 3103